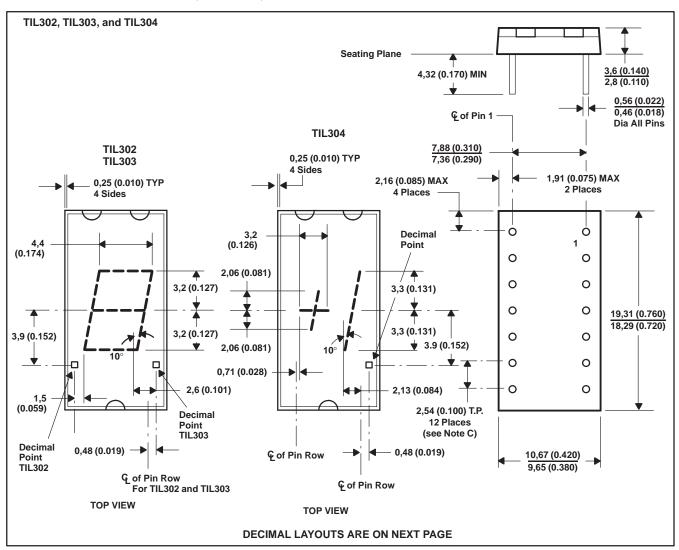
SOES010A, APRIL 1971 - REVISED DECEMBER 1993

- Red Solid-State Display
- 6,9-mm (0.270-Inch) Character Height
- High Luminous Intensity
- Low Power Requirements
- Each Unit Visually Checked for Uniformity of Elements

mechanical data

- Sign, Overflow, and Left or Right Decimal Capabilities
- Wide Viewing Angle
- Compatible With Most TTL and DTL Circuits

These assemblies consist of display chips mounted on a header with molded plastic body. Multiple displays may be mounted on 11,43-mm (0.450-inch) centers.



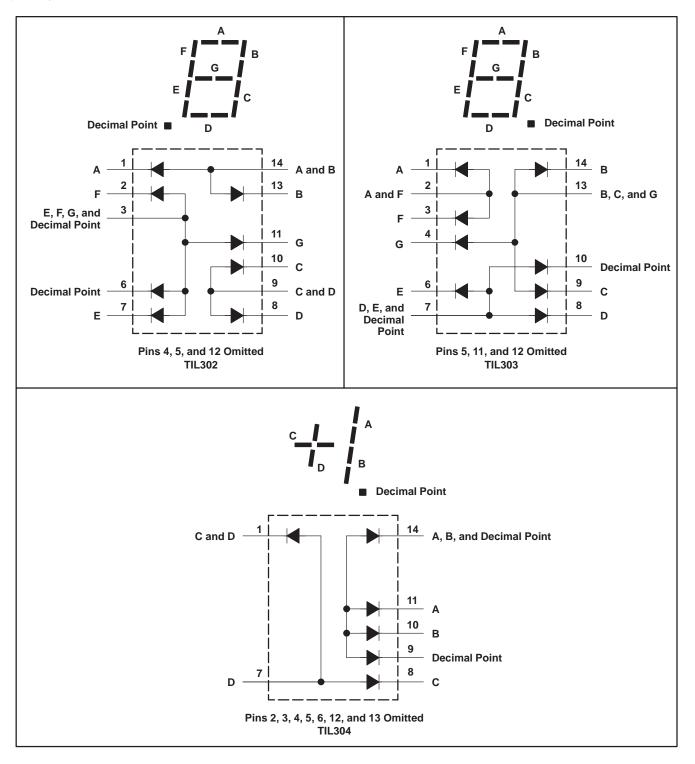
NOTES: A. All linear dimensions are in millimeters and parenthetically in inches.

- B. Centerlines of character segments are shown as dashed lines. Associated dimensions are nominal.
- C. The true-position pin spacing is 2,54 mm (0.100 inch) between centerlines. Each centerline is located within 0,26 mm (0.010 inch) of its true longitudinal position relative to pins 1 and 11.



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pin layouts





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Reverse voltage at 25°C free-air temperature: Each se	egment
Peak forward current, each segment or decimal point (se	
Continuous forward current: Each segment or decimal	ooint
Total for TIL302, TIL303	
Total for TIL304	150 mA
Operating free-air temperature range, TA	
Storage temperature range	

NOTE 1: This value applies for PRR \ge 60 Hz, duty cycle \le 10%.

operating characteristics of each segment at 25°C free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_V	Luminous intensity (see Note 2)		100	275		μcd
λp	Wavelength at peak emission	IF = 20 mA		660		nm
Δλ	Spectral bandwidth	1F = 20 MA		20		nm
٧F	Static forward voltage		3	3.4	3.8	V
αVF	Average temperature coefficient of static forward voltage	$I_F = 20 \text{ mA},$ $T_A = 0^{\circ}\text{C} \text{ to } 70^{\circ}\text{C}$	-2.7			mV/°C
I _R	Static reverse current	V _R = 6 V			100	μA
С	Anode-to-cathode capacitance	$V_R = 0$, $f = 1 MHz$		85		pF

operating characteristics of decimal point at 25°C free-air temperature (unless otherwise noted)

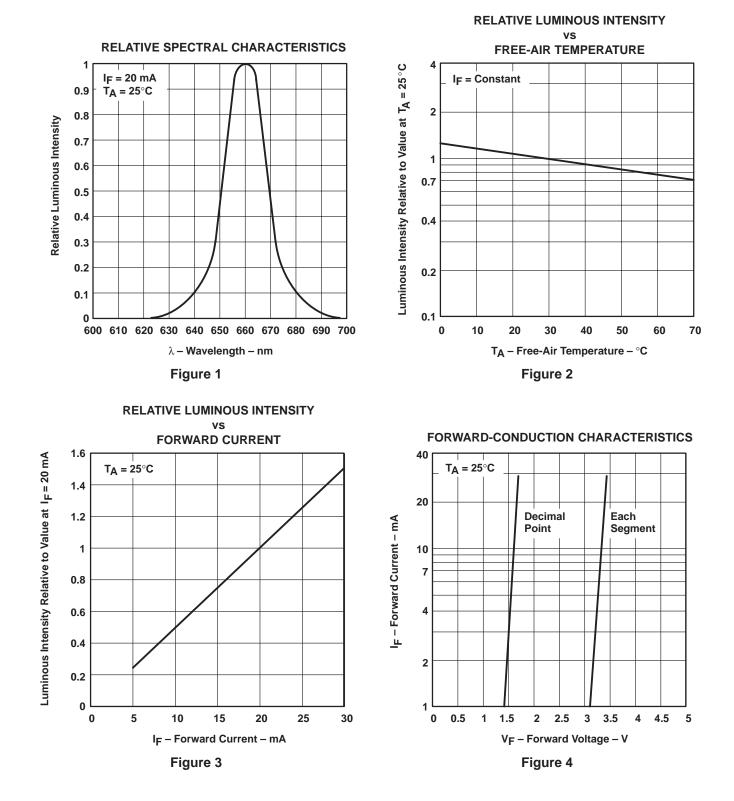
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Iv	Luminous intensity (see Note 2)		40	110		μcd
λp	Wavelength at peak emission	IF = 20 mA		660		nm
Δλ	Spectral bandwidth	F = 20 mA		20		nm
٧F	Static forward voltage		1.5	1.65	2	V
αVF	Average temperature coefficient of static forward voltage	$I_F = 20 \text{ mA},$ $T_A = 0^{\circ}C \text{ to } 70^{\circ}C$		-1.4		mV/°C
IR	Static reverse current	V _R = 3 V			100	μA
С	Anode-to-cathode capacitance	$V_R = 0$, f = 1 MHz		120		pF

NOTE 2: Luminous intensity is measured with a light sensor and filter combination that approximates the CIE (International Commission on Illumination) eye-response curve.



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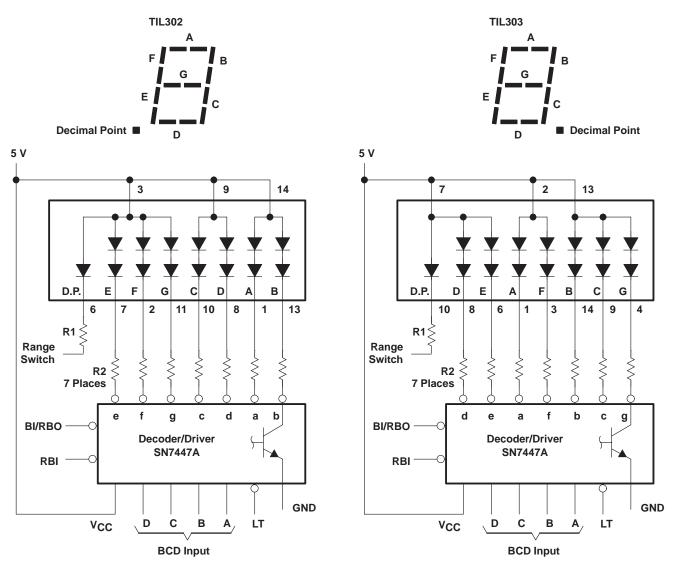






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APPLICATION INFORMATION



NOTE A: R1 and R2 are selected for desired brightness.



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APPLICATION INFORMATION

FUNCTION TABLE SN7447A

	-						5N/44/A								
DECIMAL	INPUTS						,	SEGMENTS							NOTE
OR FUNCTION	LT	RBI	D	С	В	А	BI/RBO†	а	b	с	d	е	f	g	NOTE
0	н	Н	L	L	L	L	Н	ON	ON	ON	ON	ON	ON	OFF	1
1	н	Х	L	L	L	Н	Н	OFF	ON	ON	OFF	OFF	OFF	OFF	1
2	н	Х	L	L	Н	L	Н	ON	ON	OFF	ON	ON	OFF	ON	1
3	н	Х	L	L	Н	Н	Н	ON	ON	ON	ON	OFF	OFF	ON	1
4	н	Х	L	Н	L	L	Н	OFF	ON	ON	OFF	OFF	ON	ON	1
5	н	Х	L	Н	L	Н	Н	ON	OFF	ON	ON	OFF	ON	ON	1
6	н	Х	L	Н	Н	L	Н	OFF	OFF	ON	ON	ON	ON	ON	1
7	Н	Х	L	Н	Н	Н	Н	ON	ON	ON	OFF	OFF	OFF	OFF	1
8	Н	Х	Н	L	L	L	Н	ON	ON	ON	ON	ON	ON	ON	1
9	н	Х	н	L	L	Н	Н	ON	ON	ON	OFF	OFF	ON	ON	1
10	н	Х	н	L	Н	L	Н	OFF	OFF	OFF	ON	ON	OFF	ON	1
11	Н	Х	н	L	Н	Н	Н	OFF	OFF	ON	ON	OFF	OFF	ON	1
12	н	Х	Н	Н	L	L	Н	OFF	ON	OFF	OFF	OFF	ON	ON	1
13	н	Х	н	Н	L	Н	Н	ON	OFF	OFF	ON	OFF	ON	ON	1
14	н	Х	н	Н	Н	L	Н	OFF	OFF	OFF	ON	ON	ON	ON	1
15	н	Х	Н	Н	Н	Н	Н	OFF	OFF	OFF	OFF	OFF	OFF	OFF	1
BI	Х	Х	Х	Х	Х	Х	L	OFF	OFF	OFF	OFF	OFF	OFF	OFF	2
RBI	н	L	L	L	L	L	L	OFF	OFF	OFF	OFF	OFF	OFF	OFF	3
LT	L	Х	Х	Х	Х	Х	Н	ON	ON	ON	ON	ON	ON	ON	4

H = high level (logic 1 in positive logic), L = low level (logic 0 in positive logic), X = irrelevant

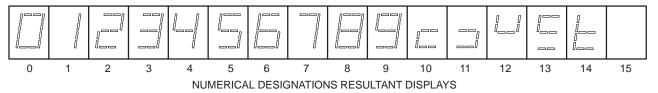
[†]BI/RBO is a wire-AND logic serving as a blanking input (BI) and/or ripple-blanking output (RBO).

NOTES: 1. The blanking input (BI) must be open or held at a high logic level when output functions 0 through 15 are desired. The ripple-blanking input (RBI) must be open or high if blanking of a decimal zero is not desired.

2. When a low logic level is applied directly to the blanking input (BI), all segment outputs are off regardless of any other input.

3. When the ripple-blanking input (RBI) and inputs A, B, C, and D are at a low logic level with the lamp-test input (LT) high, all segment outputs are off and the ripple-blanking output (RBO) of the decoder goes to a low level (response condition).

4. When the blanking input/ripple-blanking output (BI/RBO) is open or held high and a low is applied to the lamp-test input (LT), all segments are illuminated.





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